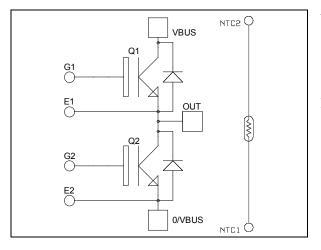
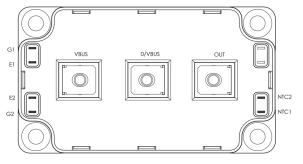


 $V_{CES} = 1200V$ $I_{C} = 400A$ @ Tc = 80°C

Phase leg High speed Trench + Field Stop IGBT4 Power module





Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- High speed Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching lossesSoft recovery parallel diodes
 - Low diode VF
 - RBSOA and SCSOA rated
- Kelvin source for easy drive
- Very low stray inductance
- M5 power connectors
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Voltage		1200	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	625	
I _C	Continuous Conector Current	$T_C = 80^{\circ}C$	400	Α
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	1250	
V _{GE}	Gate – Emitter Voltage		±20	V
P _D	Maximum Power Dissipation	$T_C = 25^{\circ}C$	1900	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	800A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				200	μA
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		2.05	2.4	V
V _{CE(sat)}		$I_{\rm C} = 400 {\rm A}$	$T_{j} = 150^{\circ}C$		2.6		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 14 \text{ mA}$		5.2	5.8	6.4	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				680	nA

Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			24.6		
C _{oes}	Output Capacitance	$V_{CE} = 25V$			1.4		nF
C _{res}	Reverse Transfer Capacitance	f = 1 MHz			1.2		
Q _G	Gate charge	V_{GE} = 15V ; V_{CE} I_C =400A	=960V		1800		nC
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)			30		
Tr	Rise Time	$V_{GE} = \pm 15V$			57		
T _{d(off)}	Turn-off Delay Time	$V_{CE} = 600V$ $I_{C} = 400A$			290		ns
T _f	Fall Time	$R_{G} = 1.25\Omega$			16		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C)			30		
T _r	Rise Time	$V_{GE} = \pm 15V$ $V_{CE} = 600V$			49		ns
T _{d(off)}	Turn-off Delay Time	$I_{\rm C} = 400 {\rm A}$			366		115
T _f	Fall Time	$R_G = 1.25\Omega$			48		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$	$T_J = 150^{\circ}C$		36		mJ
E _{off}	Turn-off Switching Energy	$I_{\rm C} = 400 \text{A}$ $R_{\rm G} = 1.25 \Omega$	$T_J = 150^{\circ}C$		22		mJ
I _{sc}	Short Circuit data	$\begin{array}{l} V_{GE} \leq \!\! 15V ; V_{Bus} = 600V \\ t_p \leq \!\! 10\mu s \; ; \; T_j = 150^{\circ}C \end{array}$			1400		А
R _{thJC}	Junction to Case Thermal Resistance					0.08	°C/W

Diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Repetitive Reverse Voltage					1200	V
I _{RM}	Reverse Leakage Current	V _R =1200V				250	μΑ
$I_{\rm F}$	DC Forward Current		$T_{\rm C} = 50^{\circ}{\rm C}$		400		А
V		$I_{\rm F} = 400 {\rm A}$	$T_j = 25^{\circ}C$		1.9	2.2	V
$V_{\rm F}$	Diode Forward Voltage	$V_{GE} = 0V$	$T_{j} = 150^{\circ}C$		1.85		v
+	Deverse Deservery Time		$T_j = 25^{\circ}C$		155		ns
t _{rr}	Reverse Recovery Time	1 400 4	$T_{j} = 150^{\circ}C$		300		
0	Reverse Recovery Charge	$I_{\rm F} = 400 \text{A}$ $V_{\rm R} = 600 \text{V}$	1 = 25°(1)		37.2		
Q _{rr}	Reverse Recovery Charge		$T_{j} = 150^{\circ}C$		78		μC
Er	Reverse Recovery Energy	Reverse Recovery Energy		$T_j = 25^{\circ}C$	16		mJ
Ľ	Reverse Recovery Energy		$T_{j} = 150^{\circ}C$		32		1115
R _{thJC}	Junction to Case Thermal Resistance					0.14	°C/W

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Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

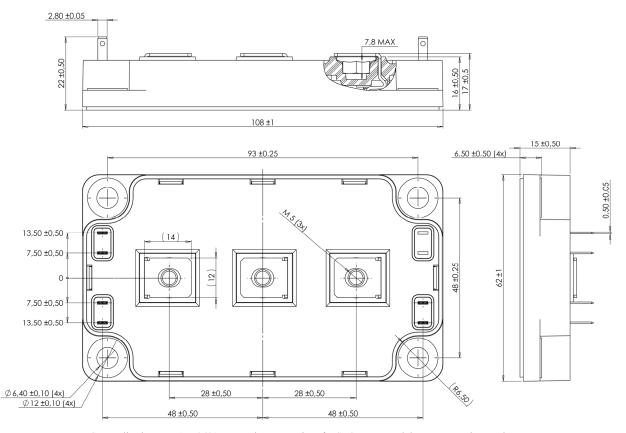
Symbol	Characteristic	,	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		Κ
$\Delta B/B$		$T_C=100^{\circ}C$		4		%
	n					

 $R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$ T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case		4000		V	
T _J	Operating junction temperature range			-40	175	
T _{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25	°C
T _{STG}	T _{STG} Storage Temperature Range				125	C
T _C	Operating Case Temperature		-40	100		
Torque	Mounting torque	To Heatsink	M6	3	5	N.m
rorque	Mounting torque	For teminals M5		2	3.5	19.111
Wt	Package Weight				300	g

Package outline (dimensions in mm)



See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

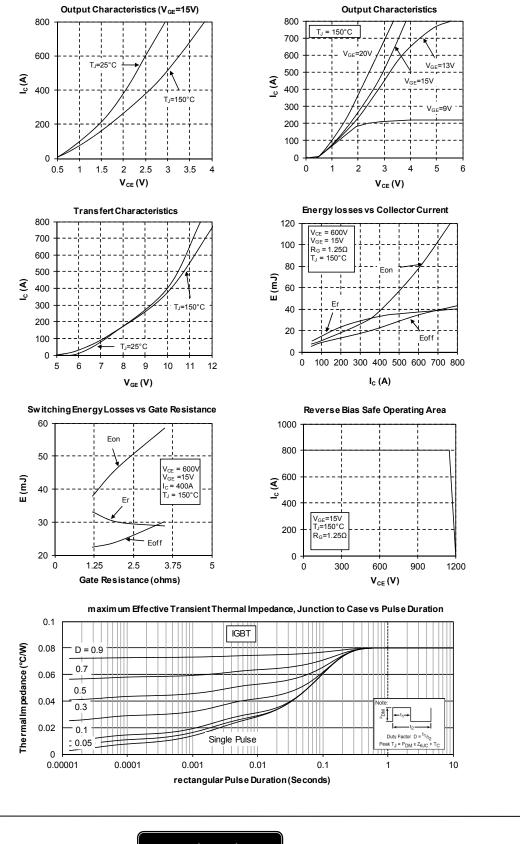
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Typical Performance Curve



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TJ=25°C

2.5

TJ=150°C

1 $V_F(V)$

> Note ₽G

-t₁

Duty Factor D = t_{1/t_2}

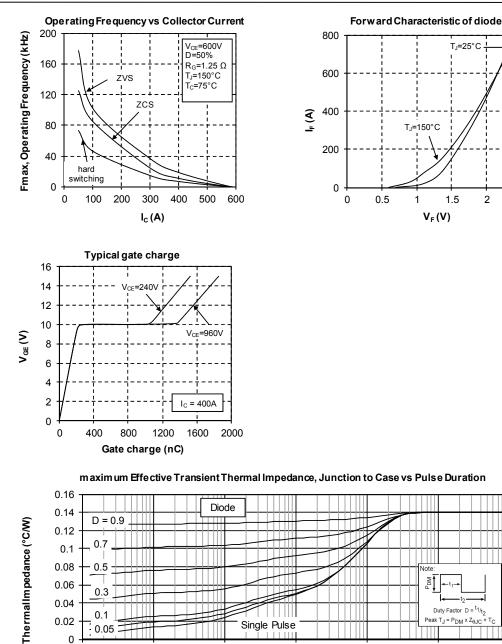
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Peak T_J = P_{DM} × Z_{θJC}

1

1.5

2



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Single Pulse

0.01

Rectangular Pulse Duration (Seconds)

0.1

0.001

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0.1

0.05 =

0.0001

0.02

0 0.00001



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